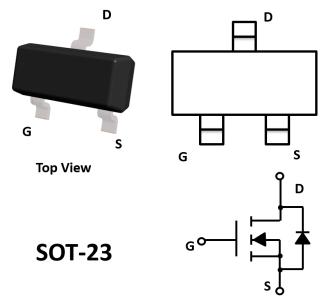




N-Channel Enhancement Mode Field Effect Transistor



Product Summary

 $\begin{array}{lll} \bullet \ V_{DS} & 30V \\ \bullet \ I_{D} & 5.6A \\ \bullet \ R_{DS(ON)} (\ at \ V_{GS} = 10V) & <29 \ mohm \\ \bullet \ R_{DS(ON)} (\ at \ V_{GS} = 4.5V) & <40 \ mohm \\ \end{array}$

General Description

- Trench Power LV MOSFET technology
- High density cell design for low RDS(ON)
- High Speed switching

Applications

- Battery protection
- Load switch
- Power management

■ Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-source Voltage		V _{DS}	30	V	
Gate-source Voltage		V_{GS}	±20	V	
Drain Current	T _A =25℃ @ Steady State		5.6	А	
	T _A =70°C @ Steady State	I _D	4.5		
Pulsed Drain Current ^A		I _{DM}	30	Α	
Total Power Dissipation @ T _A =25℃		P _D	1.2	W	
Thermal Resistance Junction-to-Ambient @ Steady State ^B		R_{\thetaJA}	104	°C/W	
Junction and Storage Temperature Range		T _J ,T _{STG}	<i>-</i> 55∼+150	$^{\circ}$	

■ Ordering Information (Example)

PREFERED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJL3404A	F2	R4.	3000	30000	120000	7" reel



YJL3404A

■ Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Тур	Max	Units	
Static Parameter							
Drain-Source Breakdown Voltage	BV_{DSS}	V _{GS} = 0V, I _D =250μA	30			V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V,V _{GS} =0V			1	μΑ	
Gate-Body Leakage Current	I _{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			±100	nA	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_{D}=250\mu A$	1	1.5	2.2	V	
Otatia Basia Ocurso Oc Basiatana		V _{GS} =10V, I _D =5.6A		21	29	mΩ	
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} = 4.5V, I _D =5.0A		27	40		
Diode Forward Voltage	V _{SD}	I _S =5.6A,V _{GS} =0V		0.8	1.2	V	
Maximum Body-Diode Continuous Current	Is				5.6	А	
Dynamic Parameters							
Input Capacitance	C _{iss}			490		pF	
Output Capacitance	C _{oss}	V _{DS} =15V,V _{GS} =0V,f=1MHZ		92			
Reverse Transfer Capacitance	C _{rss}			68			
Switching Parameters							
Total Gate Charge	Q_g			5.2		nC	
Gate Source Charge	Q_gs	V _{GS} =10V,V _{DS} =15V,I _D =5.6A		0.9			
Gate Drain Charge	Q_{gd}			1.3			
Turn-on Delay Time	t _{D(on)}			4.5			
Turn-on Rise Time	t _r	V _{GS} =4.5V,V _{DD} =15V, I _D =1A,		2.5		- ns	
Turn-off Delay Time	$t_{D(off)}$	R_{GEN} =2.8 Ω		14.5			
Turn-off Fall Time	t _f			3.5			

A. Pulse Test: Pulse Width \leq 300us, Duty cycle \leq 2%.

B. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.



■ Typical Performance Characteristics

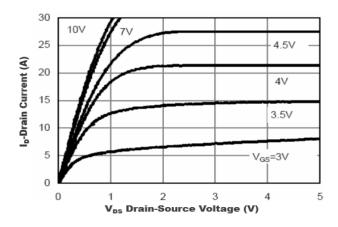


Figure 1. Output Characteristics

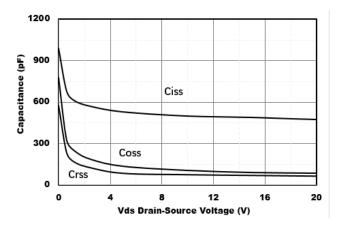


Figure 3. Capacitance Characteristics

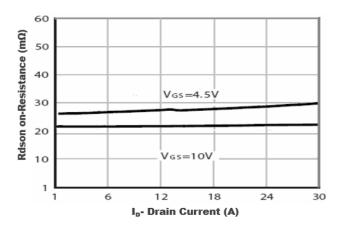


Figure 5. Drain-Source on Resistance

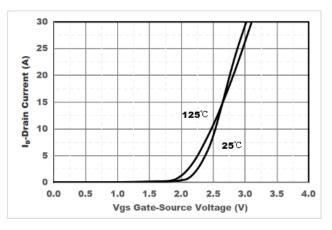


Figure 2. Transfer Characteristics

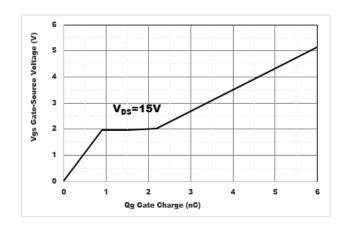


Figure 4. Gate Charge

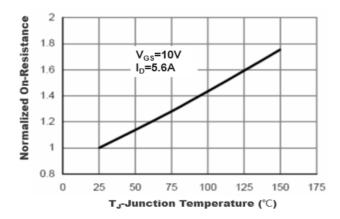


Figure 6. Drain-Source on Resistance





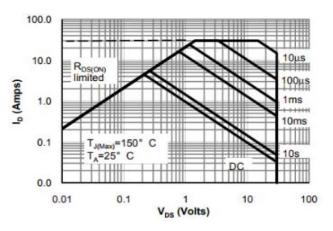


Figure 7. Safe Operation Area

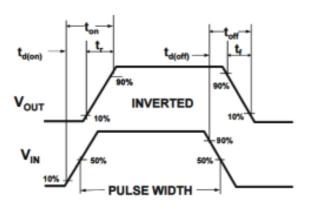
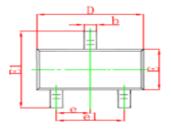
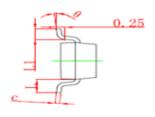


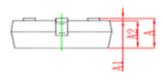
Figure8. Switching wave



■ SOT-23 Package information

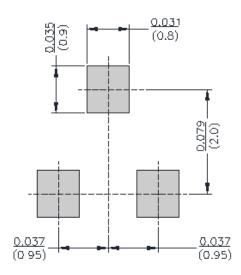






Symbol	Dimentions in Millimeter		Dimentions in Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.100	0.200	0.004	0.008	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950Type		0.037Type		
e1	1.800	2.000	0.071	0.079	
L	0.550REF		0.220REF		
L1	0.300	0.500	0.012	0.020	
θ	0 °	8 °	0 °	8 °	

■ SOT-23 Suggested Pad Layout





YJL3404A

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